



2N7002A

N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

- N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- · Fast Switching Speed
- Small Surface Mount Package
- ESD Protected Gate, 1.2kV HBM
- Lead, Halogen and Antimony Free, RoHS Compliant "Green" Device (Notes 2 and 4)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

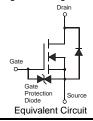
- Case: SOT-23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Copper leadframe).
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)

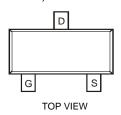




TOP VIEW

SOT-23





Maximum Ratings @T_A = 25°C unless otherwise specified

Characterist	Symbol	Value	Units	
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage (Note 1)	Continuous	V_{GSS}	±20	V
Drain Current (Note 1)	Continuous Continuous @ 100°C Pulsed	I _D	115 73 800	mA

Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation	Б	250	mW
Derating above T _A = 25°C (Note 1)	PD	1.6	mW/°C
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	500	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C

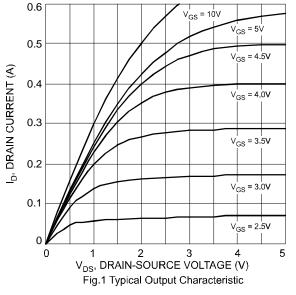
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 3)							
Drain-Source Breakdown Voltage		BV _{DSS}	60	70		>	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	@ T _C = 25°C @ T _C = 125°C	I _{DSS}		_	1.0 500	μΑ	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Body Leakage		I _{GSS}		_	±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 3)							
Gate Threshold Voltage		V _{GS(th)}	1.2		2.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance	@ T _J = 25°C @ T _J = 125°C	R _{DS} (ON)	_	3.5 3.0	6 5	Ω	$V_{GS} = 5.0V, I_D = 0.115A$ $V_{GS} = 10V, I_D = 0.115A$
Forward Transconductance		g FS	80		_	mS	V _{DS} = 10V, I _D = 0.115A
DYNAMIC CHARACTERISTICS							
Input Capacitance		C _{iss}	_	23	_	рF	
Output Capacitance		Coss		3.4		рF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$
Reverse Transfer Capacitance		C _{rss}		1.4	_	pF	
SWITCHING CHARACTERISTICS							
Turn-On Delay Time		t _{D(ON)}		10	_	ns	$V_{DD} = 30V$, $I_D = 0.115A$, $R_L = 150\Omega$,
Turn-Off Delay Time		t _{D(OFF)}	_	33	_	ns	$V_{GEN} = 10V, R_{GEN} = 25\Omega$

Notes:

- 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 2. No purposefully added lead. Halogen and Antimony Free.
- 3. Short duration pulse test used to minimize self-heating effect.
- 4. Product manufactured with Data Code V9 (week 33, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V9 are built with Non-Green Molding Compound and may contain Halogens or Sb203 Fire Retardants.





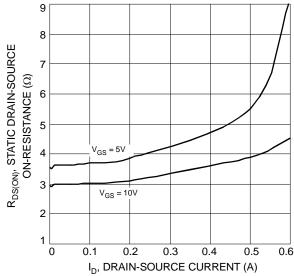


Fig. 3 On-Resistance vs. Drain Current & Gate Voltage

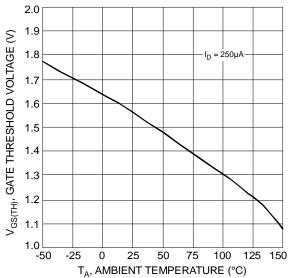
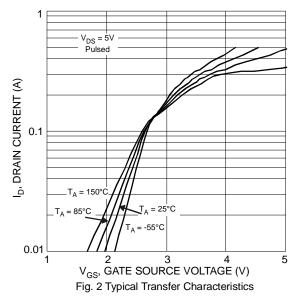


Fig. 5 Gate Threshold Variation vs. Ambient Temperature



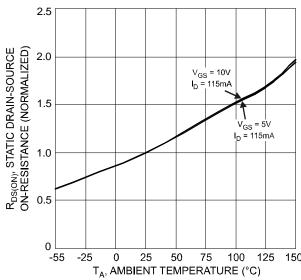


Fig. 4 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

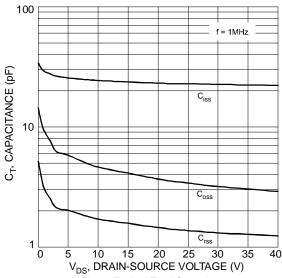


Fig. 6 Typical Total Capacitance



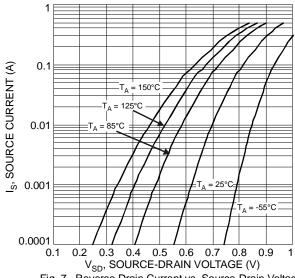


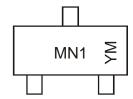
Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

Ordering Information (Note 5)

Part Number	Case	Packaging
2N7002A-7	SOT-23	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



MN1 = Product Type Marking Code YM = Date Code Marking

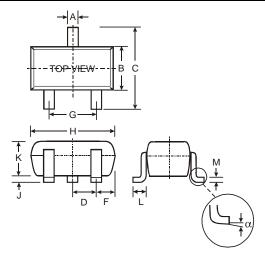
Y = Year ex: V = 2008

M = Month ex: 9 = September

Date Code Key

Year	2008		2009	2010		2011	2012		2013	2014		2015
Code	V		W	Х		Υ	Z		Α	В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

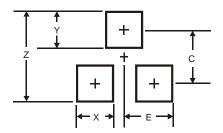
Package Outline Dimensions



SOT-23					
Dim	Min	Max			
Α	0.37	0.51			
В	1.20	1.40			
C	2.30	2.50			
D	0.89	1.03			
F	0.45	0.60			
G	1.78	2.05			
Н	2.80	3.00			
7	0.013	0.10			
K	0.903	1.10			
٦	0.45	0.61			
M	0.085	0.180			
α	0°	8°			
All Dir	All Dimensions in mm				



Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
E	1.35

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